

- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ 100% EAS Guaranteed
- ★ Advanced high cell density Trench technology

Product Summary

RoHS

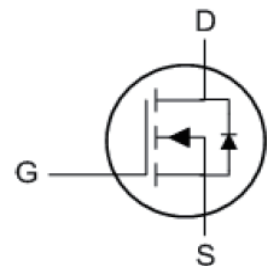
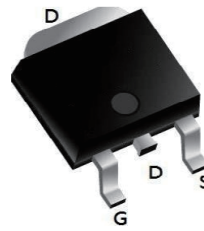
BVDSS	RDSON	ID
40V	11mΩ	45A

Description

The 50N04 is the high cell density trenched N ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 50N04 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS}@ 10V^1$	45	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS}@ 10V^1$	25	A
I_{DM}	Pulsed Drain Current ²	80	A
EAS	Single Pulse Avalanche Energy ³	19	mJ
I_{AS}	Avalanche Current	30	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	20	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	55	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4.32	$^\circ C/W$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=10V, I_D=8A$	-	11	16	m Ω
		$V_{GS}=4.5V, I_D=4A$	-	18.9	24	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5V, I_D=8A$	33	-	-	S
Dynamic Characteristics (Note 4)						
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, F=1.0MHz$	-	964	-	PF
C_{oss}	Output Capacitance		-	109	-	PF
C_{rss}	Reverse Transfer Capacitance		-	96	-	PF
Switching Characteristics (Note 4)						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=20V, R_L=2.5\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	5.5	-	nS
t_r	Turn-on Rise Time		-	14	-	nS
$t_{d(off)}$	Turn-Off Delay Time		-	24	-	nS
t_f	Turn-Off Fall Time		-	12	-	nS
Q_g	Total Gate Charge	$V_{DS}=20V, I_D=8A, V_{GS}=10V$	-	22.9	-	nC
Q_{gs}	Gate-Source Charge		-	3.5	-	nC
Q_{gd}	Gate-Drain Charge		-	5.3	-	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage (Note 3)	$V_{GS}=0V, I_S=9A$	-	0.8	1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

N-Channel Typical Electrical and Thermal Characteristics (Curves)

Figure 1: Switching Test Circuit

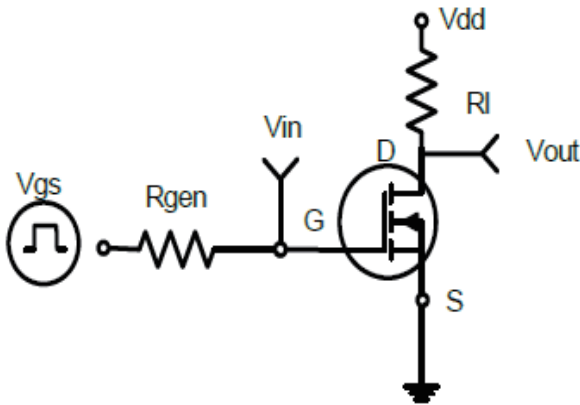


Figure 2: Switching Waveforms

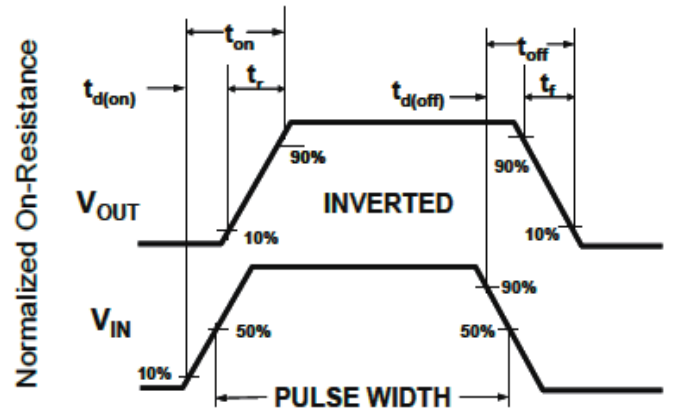


Figure 3: Output Characteristics

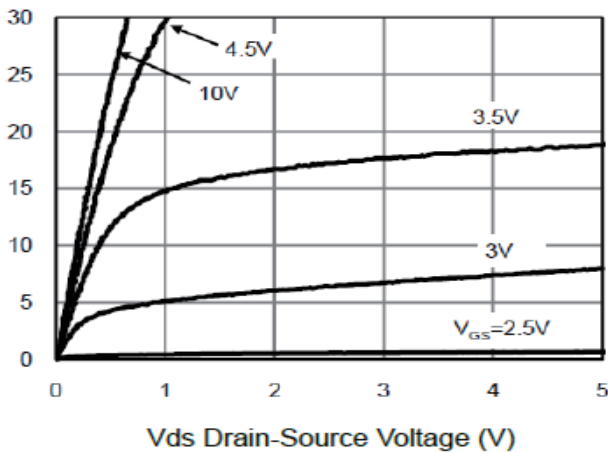


Figure 4: Transfer Characteristics

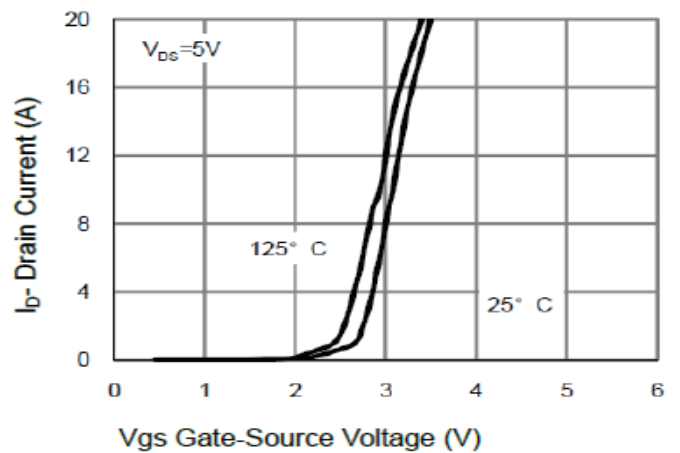


Figure 5: Drain-Source On-Resistance

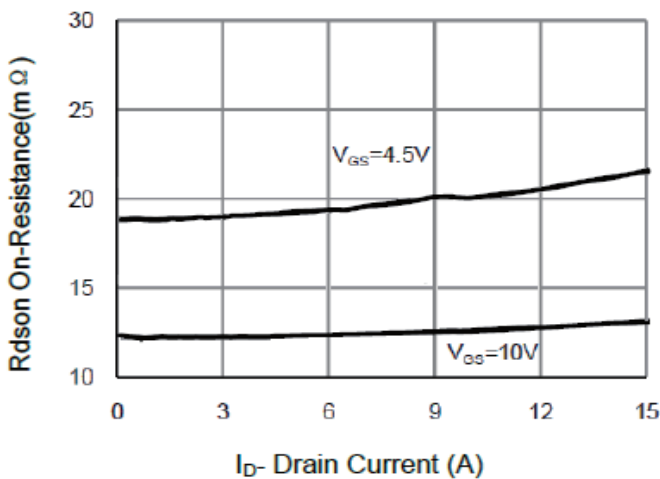
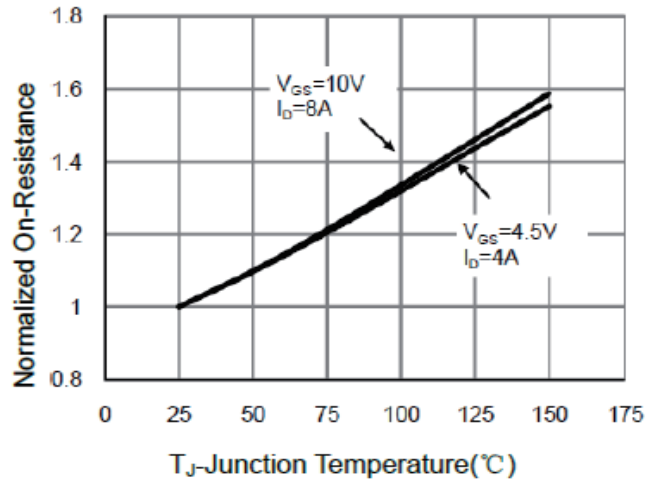


Figure 6: Drain-Source On-Resistance



Typical Performance Characteristics

Figure 7: R_{ds(on)} vs V_{gs}

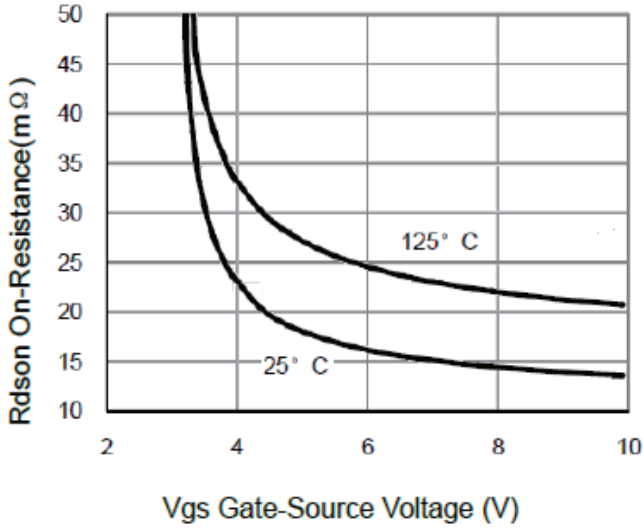


Figure 8: Power Dissipation

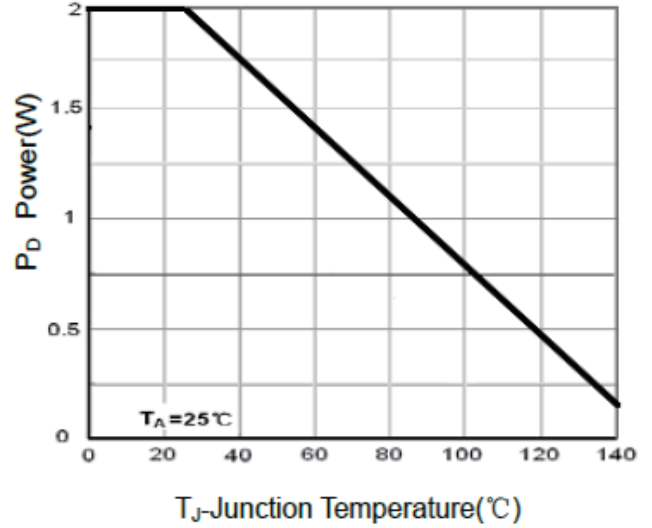


Figure 9: Gate Charge

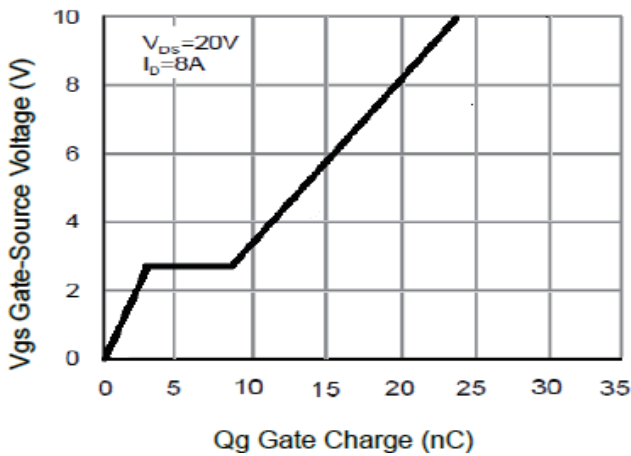


Figure 10: Source- Drain Diode Forward

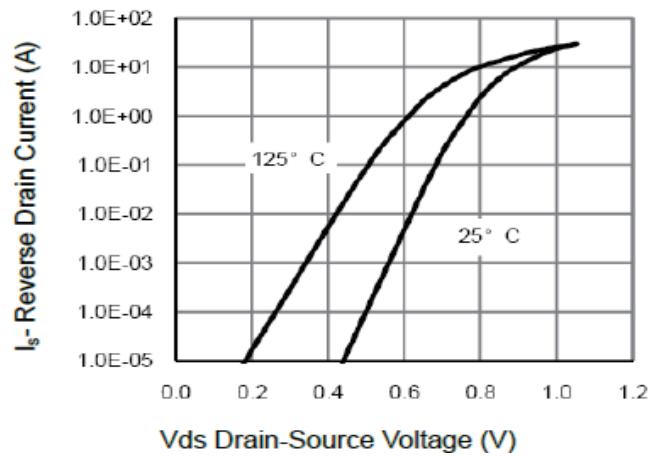


Figure 11: Capacitance vs V_{ds}

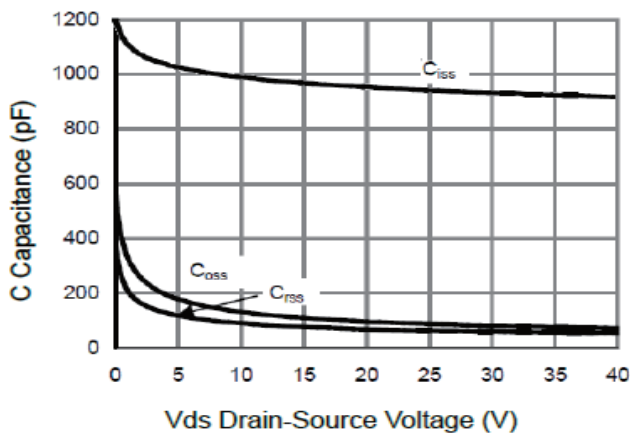
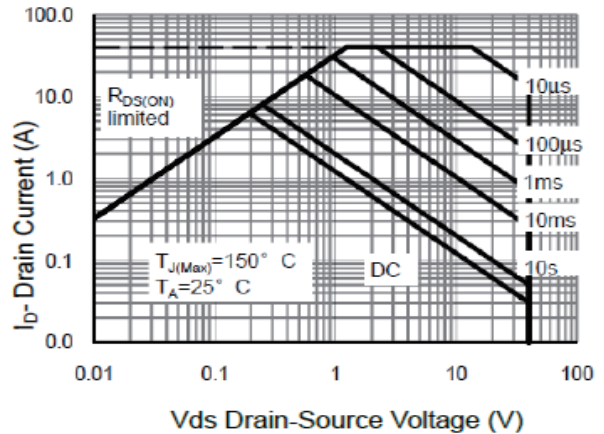
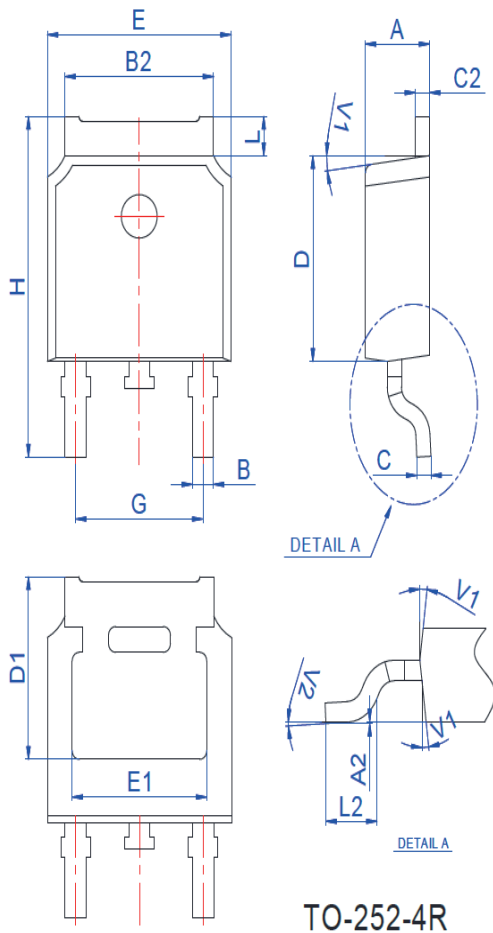


Figure 12: Safe Operation Area

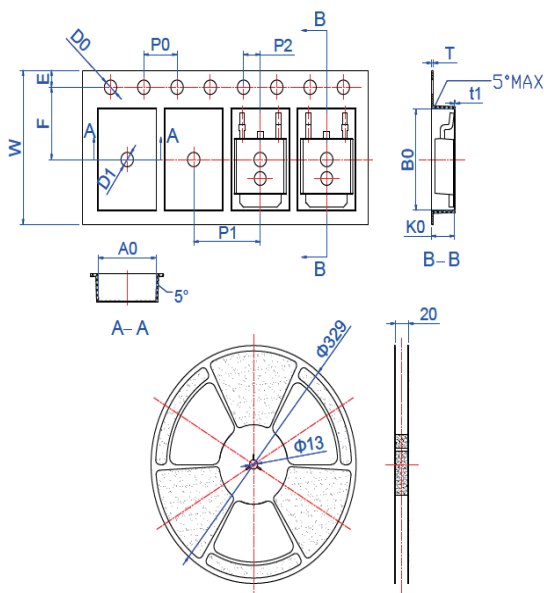


Package Mechanical Data-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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